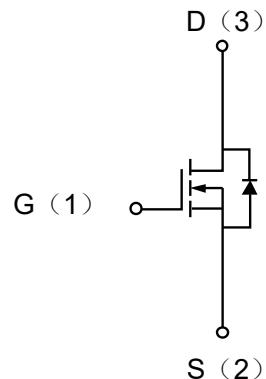


Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

Package: SOT-23

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
60	0.096@ V _{GS} =4.5V	3



Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF/ON CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
		V _{DS} =60V, V _{GS} =0V T _J =55°C			10	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	-	2.0	V
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =4.5V, I _D =2.1A	-	0.096	0.140	Ω
		V _{GS} =10V, I _D =2.6A	-	0.082	0.110	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, f=1MHz	-	350		pF
Output Capacitance	C _{oss}		-	40		pF
Reverse Transfer Capacitance	C _{rss}		-	12		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DS} =20V, V _{GS} =10V, R _G =1Ω, R _L =20Ω I _D =1A	-	10		ns
Turn-Off Delay Time	t _{d(off)}		-	29		ns
Turn-On Rise Time	t _r		-	11		ns
Turn-On Fall Time	t _f		-	3		ns
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =10V, I _D =2.6A		12		nC
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =4.5V, I _D =2.6A		6.5		nC
Gate-Source Charge	Q _{gs}			2.2		nC
Gate-Drain Charge	Q _{gd}			2.7		nC
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1.0A		0.8	1.2	V

Absolute maximum rating@25°C

Parameter	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3	A
Current($T_J=150^\circ\text{C}$)		2.1	
Pulsed Drain Current	I_{DM}	10	A
Maximum Power Dissipation	P_D	1.04	W
$T_A=70^\circ\text{C}$		0.67	
Operating Junction and Storage Temperature Range	T_J	-55 to 150	°C
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	100	°C/W

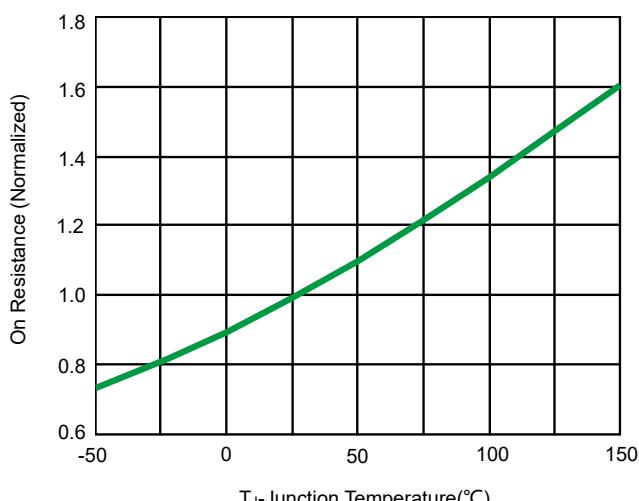
Typical Characteristics

Fig 1. On Resistance vs. Junction Temperature

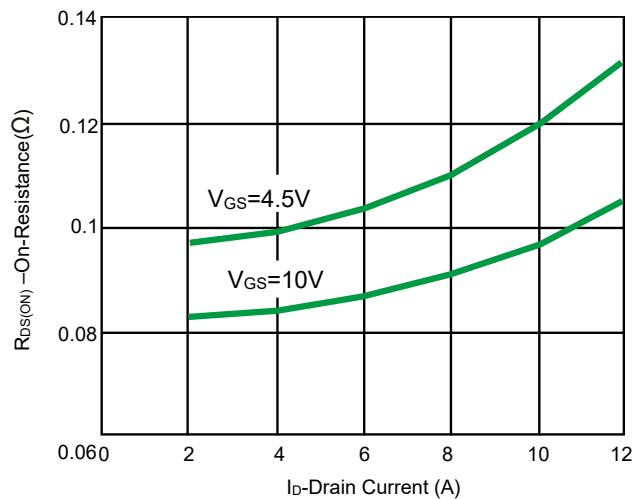


Fig 2. On-Resistance vs. Drain Current

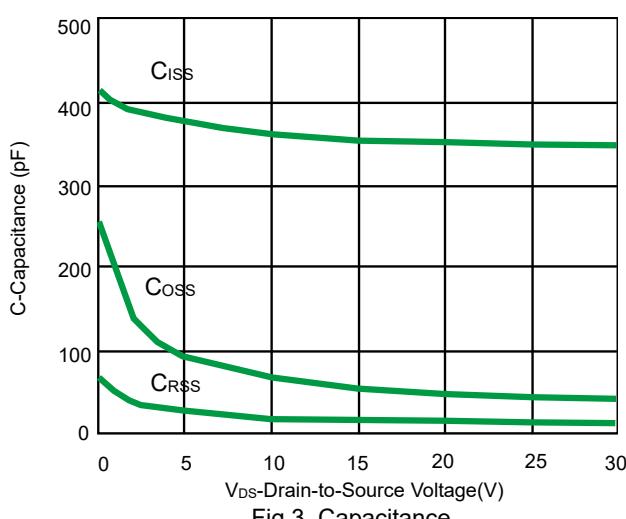


Fig 3. Capacitance

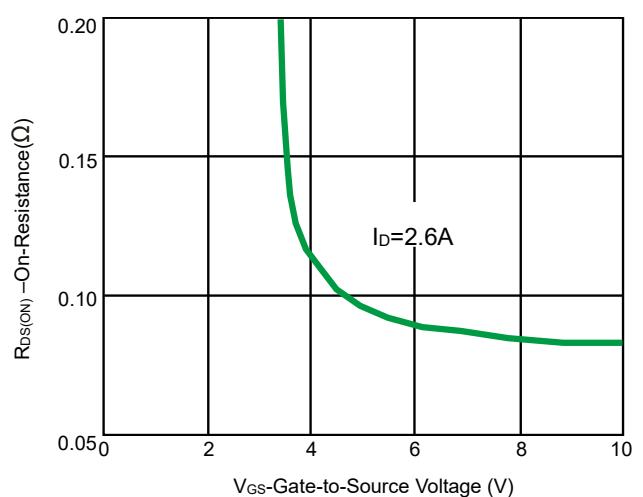


Fig 4. On-Resistance vs. Gate-to-Source Voltage

N-Channel MOSFET

PNMT60V3

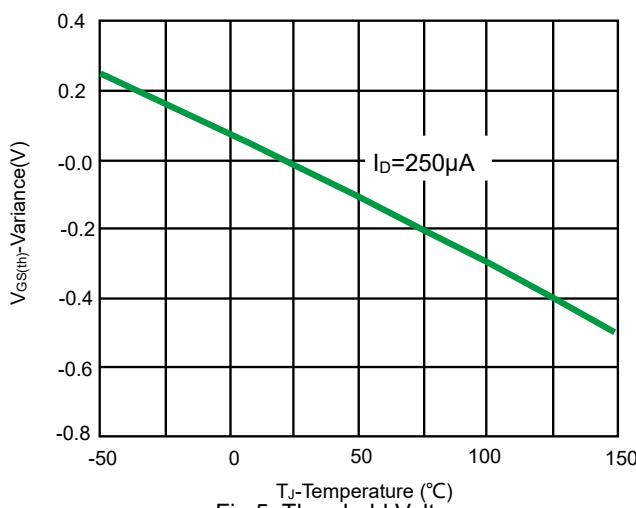


Fig 5. Threshold Voltage

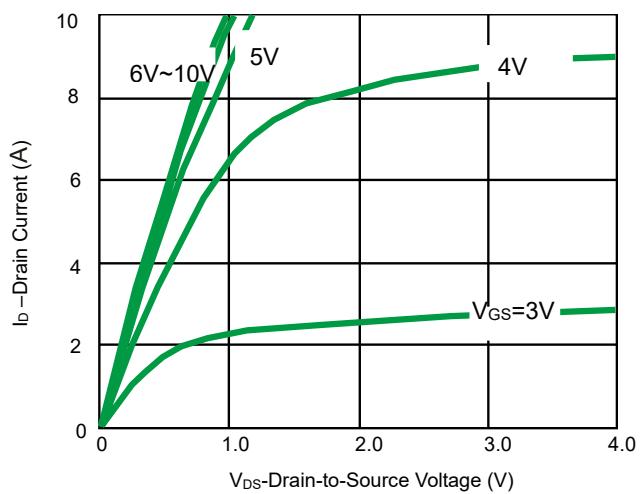


Fig 6. On-Region Characteristics

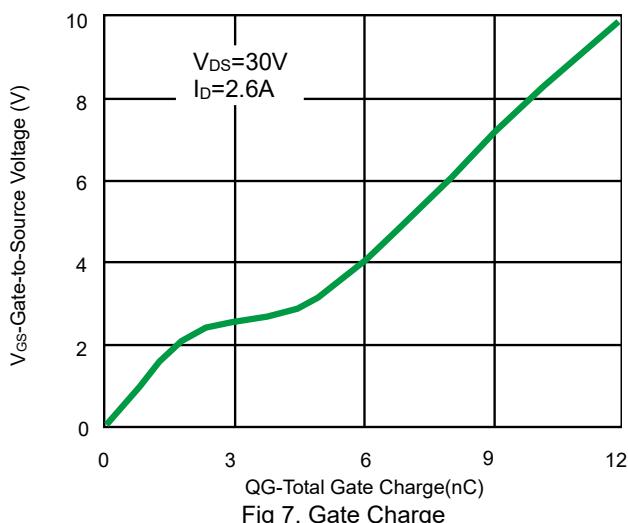


Fig 7. Gate Charge

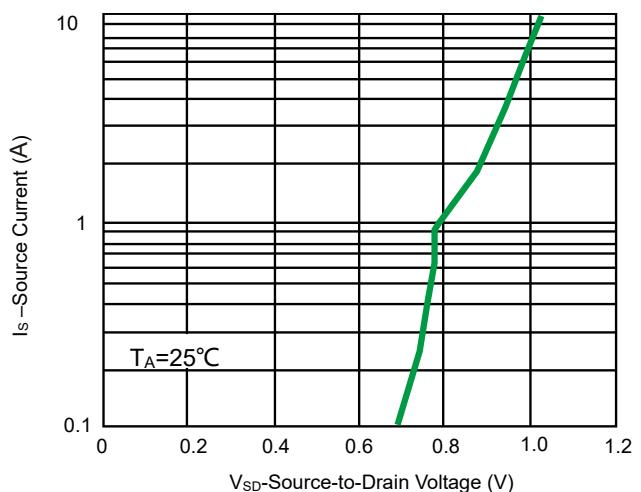


Fig 8. On-Resistance vs. Drain Current

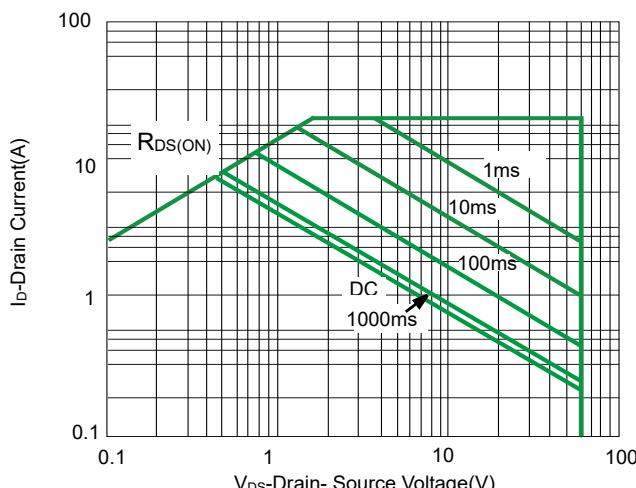


Fig 9. Maximum Forward Biased Safe Operating Area

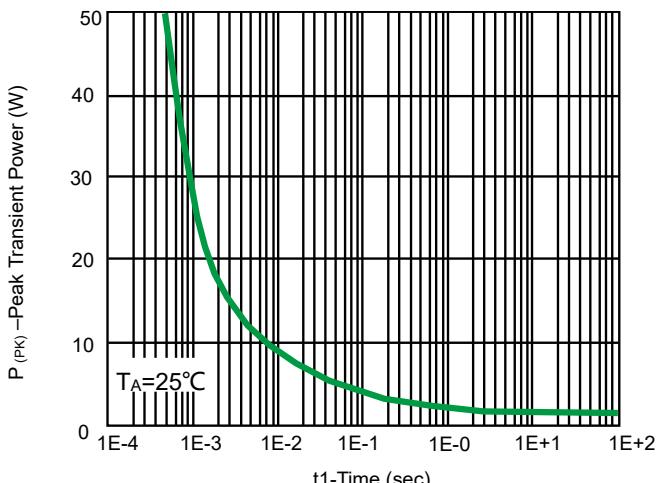


Fig 10. Single Pulse Maximum Power Dissipation

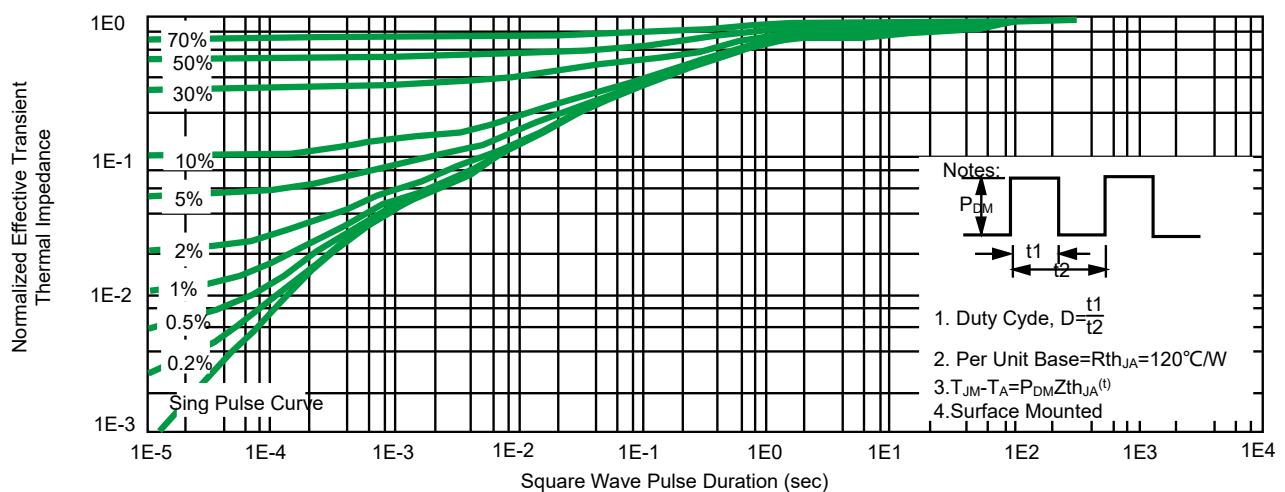
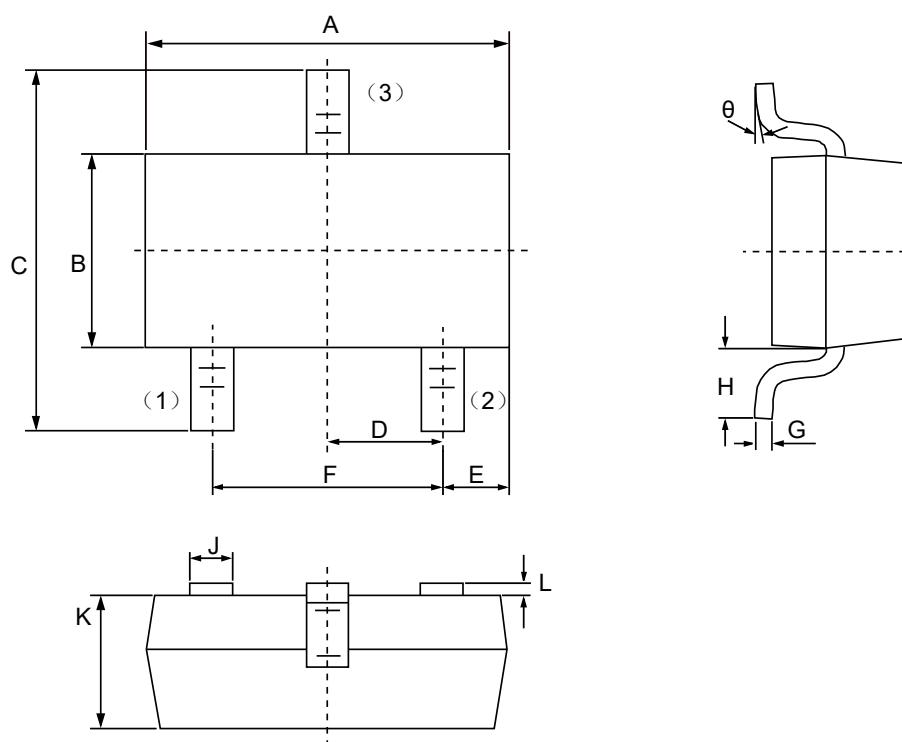
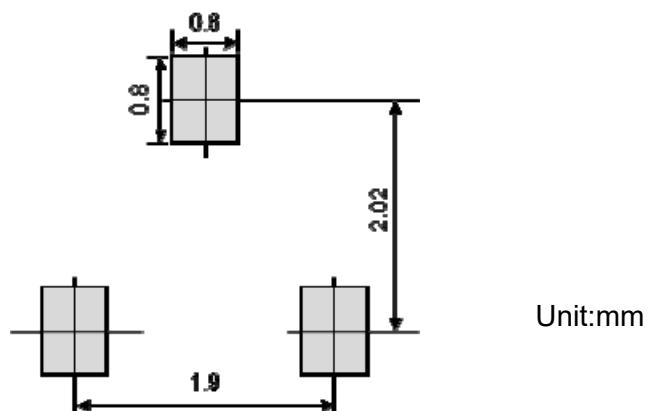


Fig 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

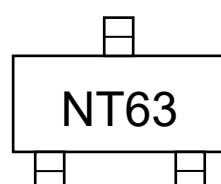
Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°



Suggested PCB Layout

Marking information

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